

2SD787, 2SD788

Absolute Maximum Ratings (Ta = 25° C)

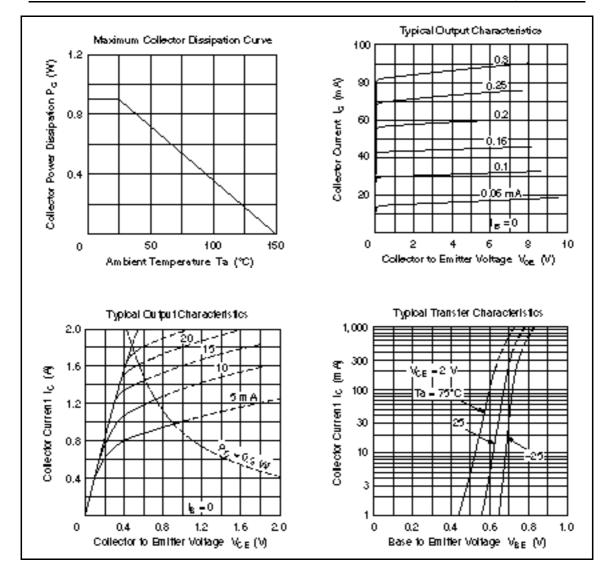
Item	Symbol	2SD787	2SD788	Unit
Collector to base voltage	V _{CBO}	20	20	V
Collector to emitter voltage	V _{CEO}	16	20	V
Emitter to base voltage	V _{EBO}	6	6	V
Collector current	I _c	2	2	А
Collector power dissipation	P _c	0.9	0.9	W
Junction temperature	Тј	150	150	°C
Storage temperature	Tstg	–55 to +150	–50 to +150	°C

Electrical Characteristics (Ta = 25°C)

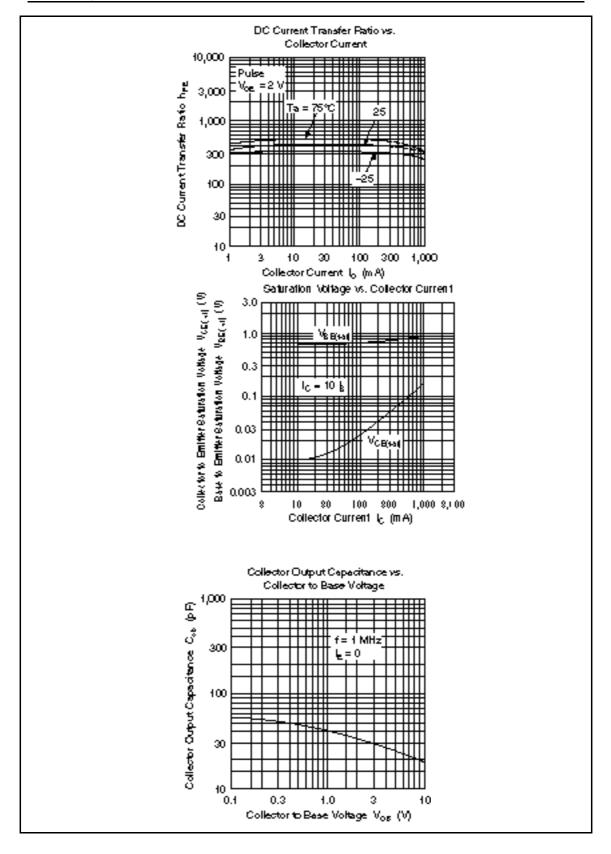
		2SD7	87		2SD788					
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions	
Collector to base breakdown voltage	$V_{\rm (BR)CBO}$	20	—	—	20	_	—	V	$I_{c} = 10 \ \mu A, \ I_{E} = 0$	
Collector to emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	16	—	—	20	_	—	V	$I_c = 1 \text{ mA}, R_{BE} =$	
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	—	—	6	—	—	V	$I_{\rm E} = 10 \ \mu {\rm A}, \ I_{\rm C} = 0$	
Collector cutoff current	I _{CBO}	_	_	2	_	_	2	μA	$V_{CB} = 16 \text{ V}, \text{ I}_{E} = 0$	
Emitter cutoff current	I _{EBO}	_	_	0.2	_	_	0.2	μA	$V_{EB} = 6 V, I_{C} = 0$	
DC current transfer ratio	h_{FE}^{*1}	100	_	800	100	_	800		$V_{ce} = 2 \text{ V}, I_c = 0.1 \text{ A}$	
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	—	0.3	—	_	0.3	V	$I_{\rm c} = 1 \text{ A}, I_{\rm B} = 0.1 \text{ A}$	
Gain bandwidth product	f _T	_	100	—	—	100	—	MHz	$V_{ce} = 2 V,$ $I_c = 10 mA$	
Collector output capacitance	Cob	_	20	—	—	20	—	pF	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0,$ f = 1 MHz	
Note: 1. The 2SD787 and 2SD788 are grouped by h _{FE} as follows.										
B C	D		Е							
100 to 200 160 to 32	0 250 t	o 500	400	to 800						

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